

New Jersey Semi-Conductor Products, Inc.

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 SPRINGFIELD, NEW JERSEY 07081
 U.S.A.

1N4154

**500mW 35 Volt
 Silicon Epitaxial Diode**

Features

- Low Current Leakage
- Compression Bond Construction
- Low Cost

Maximum Ratings

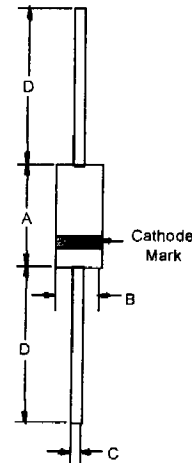
- Operating Temperature: -65°C to +175°C
- Storage Temperature: -65°C to +175°C
- Maximum Thermal Resistance; 300°C/W Junction To Ambient

Electrical Characteristics @ 25°C Unless Otherwise Specified

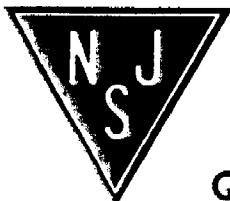
Reverse Voltage	V_R	25V	
Peak Reverse Voltage	V_{RM}	35V	
Average Rectified Current	I_O	150mA	Resistive Load $f > 50\text{Hz}$
Power Dissipation	P_{TOT}	500mW	
Junction Temperature	T_J	200°C	
Peak Forward Surge Current	I_{FSM}	500mA	8.3ms, half sine
Maximum Instantaneous Forward Voltage	V_F	1.0V	$I_{FM} = 30\text{mA};$ $T_J = 25^\circ\text{C}^*$
Maximum DC Reverse Current At Rated DC Blocking Voltage	I_R	100nA	$V_R = 25\text{Volts}$ $T_J = 25^\circ\text{C}$
Typical Junction Capacitance	C_J	4pF	Measured at 1.0MHz, $V_R = 4.0\text{V}$
Reverse Recovery Time	T_{rr}	4nS	$I_F = 10\text{mA}$ $V_R = 6\text{V}$ $R_L = 100\Omega$

*Pulse test: Pulse width 300 μsec , Duty cycle 2%

DO-35



A	—	.168	—	4.2	
B	—	.079	—	2.00	
C	—	.020	—	.52	
D	1.000	—	25.40	—	



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Quality Semi-Conductors